DMA56107

Silicon PNP epitaxial planar type

For digital circuits

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Basic Part Number

Dual DRA2124T (Common emitter)

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

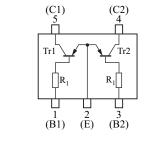
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I _C	-100	mA	
Total power dissipation	P _T	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Package

Code

- SMini5-F3-B
- Pin Name
 - 1: Base (Tr1) 4: Collector (Tr2)
 - 2: Emitter (Common) 5: Collector (Tr1)
 - $a_{2}(T_{r})$
 - 3: Base (Tr2)
- Marking Symbol: N4

Internal Connection



1	Resistance value	R ₁	22	kΩ
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Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

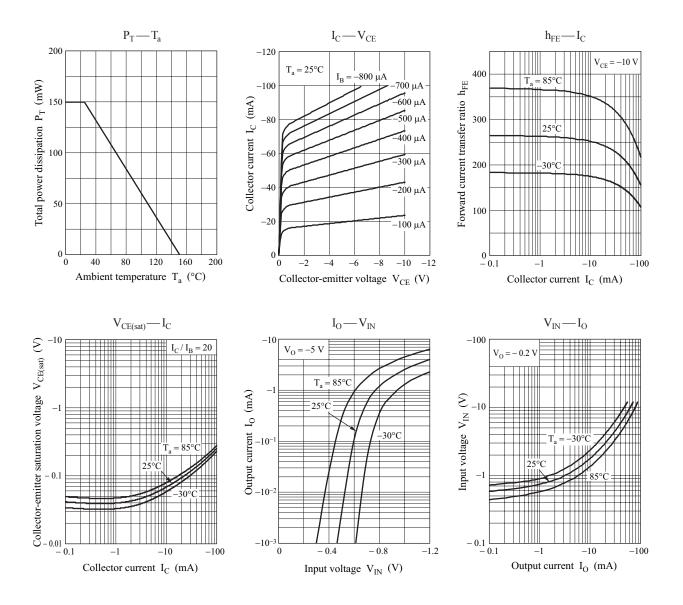
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -50 \text{ V}, I_{\rm B} = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.01	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	160		460	
h _{FE} ratio *	h _{FE} (Small/Large)	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-1.8			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			- 0.4	V
Input resistance	R ₁		-30%	22	+30%	kΩ

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Ratio between 2 elements

DMA56107

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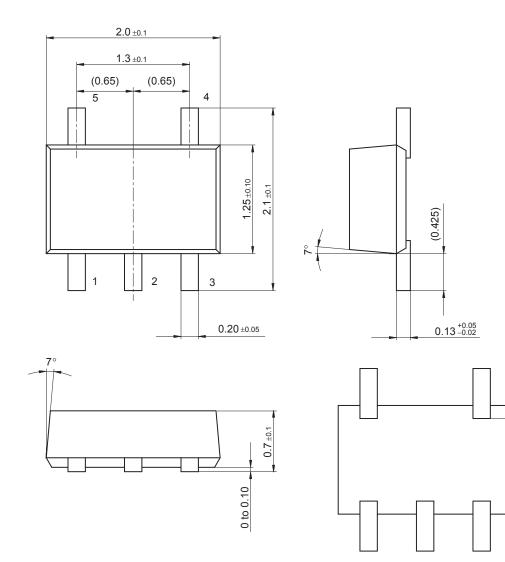


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(0.15)

SMini5-F3-B

Unit: mm



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